

## In th Claims

### Claims

1. (Previously presented) A method of preparing a polishing process liquid for a semiconductor polishing process comprising:

providing a liquid;

degassifying the liquid;

injecting a gas into the liquid to regassify the liquid, the regassification increasing a total dissolved gas concentration in the liquid to greater than or equal to 200 ppb, the regassification forming the polishing process liquid; and

wherein the injecting the gas into the degassified liquid increases the total dissolved gas concentration in the liquid to from about 450 ppb to about 550 ppb.

Claim 2 (Canceled).

3. (Previously presented) The method of Claim 1 wherein the liquid comprises water.

4. (Previously presented) The method of Claim 1 wherein the semiconductor polishing process comprises an etch process.

5. (Previously presented) The method of Claim 1 wherein the semiconductor polishing process comprises a wet etch process and the liquid comprises water.

Claims 6-38 (Canceled).

39. (Previously presented) The method of Claim 1, where degassifying the liquid comprises removing a first gas from the liquid and the gasifying the liquid comprises adding a second gas, the first gas and the second gas having different compositions.

40. (Previously presented) The method of Claim 39, where the first gas composition comprises a composition similar to that of the atmosphere and the second gas composition is an essentially non-reactive gas composition.

41. (Previously presented) The method of Claim 39, where the second gas composition comprises nitrogen and/or argon.

42. (Previously presented) The method of Claim 1, where the injected gas does not include oxygen.

Claim 43 (Canceled).

44. (Previously presented) The method of Claim 1, where injecting the gas into the degassed liquid increases the total dissolved gas concentration in the liquid to at least about 500 ppb.

45. (Previously presented) The method of Claim 1, where the providing supplies a liquid having a total dissolved concentration of oxygen that is greater than or equal to 200 ppb.

46. (Previously presented) The method of Claim 45, where the liquid provided comprises water.

47. (Previously presented) The method of Claim 1, where injecting the gas into the degassed liquid comprises injecting the gas through a sintered filter.

48. (Previously presented) The method of Claim 1, where the degassing and the regassing comprise a common processing step.